



THE UNITED STATES PATENT AND TRADEMARK OFFICE

AF/2822
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H. H. H. H. H.
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In re application of

MANABU TOMITA ET AL.

Serial No. 09/387,477 (TIJ-26105)

Filed September 1, 1999

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Art Unit 2822

Examiner M. Guerrero

Commissioner for Patents
Washington, D. C. 20231

Sir:

AMENDMENT UNDER 37 C.F.R. 1.116

In response to the Office action dated April 5, 2002, please amend the above-identified application as follows:

In the specification:

Page 5, after line 11, add the following paragraph:

"A feature of the present invention is to provide a semiconductor device manufacturing method the includes the steps of providing a semiconductor substrate having a lower electrically conducting layer thereon and an electrically insulating layer disposed over the electrically conducting layer, providing a gas etchant comprising a mixed gas of two different fluorocarbon gases, each of the fluorocarbon gases having a different ratio of carbon atoms to fluorine atoms, the fluorocarbon gas having the lower ratio of carbon atoms to fluorine atoms forming at least one half of the mixed gas and etching a connection hole through the electrically insulating layer